

Please replace the paragraph beginning at page 15, line 18, with the following rewritten paragraph:

A⁸ Next, as shown in Fig. 10B and Fig. 17C, an insulating film 34 is formed on the entire surface of the resultant structure. This insulating film 34 is formed by laminating, for example, SiON having a thickness of 200 nm and, for example, SiO₂ having a thickness of 300 nm. Thereafter, the insulating film 34 is coated with an SOG (Spin On Glass) film 35, thus flattening the surface of the resultant structure.

IN THE CLAIMS:

Please amend claims 1 and 2 as follows:

A⁹ 1. (Amended) A CMOS image sensor comprising:
a photodiode having an impurity region having source and drain regions formed respectively in semiconductor substrate; and
first and second MOS transistors formed by introducing impurities into said semiconductor substrate, and
an insulating film formed on the first and second MOS transistors, the insulating film having contact holes reaching the source regions and drain regions of the first and second MOS transistors,
wherein a silicide film is not formed on a surface of the drain region of the first MOS transistor which connects to the impurity region of the photodiode, but the silicide film is formed on a surface of the source region of the first MOS transistor which is also the drain region of the second MOS transistor and on a surface of the drain region of the second MOS transistor.

2. (Amended) A CMOS image sensor comprising:
a photodiode having an impurity region formed in semiconductor substrate;
a first MOS transistor formed on said semiconductor substrate, the first MOS transistor having an impurity region as a drain connected to said impurity region of said photodiode;
a second MOS transistor formed on said semiconductor substrate, the second MOS transistor having an impurity region as a source connected to a source of said first MOS transistor;
a third MOS transistor formed on said semiconductor substrate, the third MOS transistor having an impurity region as a source connected to a drain of said second MOS transistor, and
an insulating film formed on the first, second and third MOS transistors, the insulating film having contact holes reaching the sources and drains of the first, second and third MOS transistors,
wherein a silicide film is not formed on a surface of the drain of the first MOS transistor, but the silicide film is formed on each surface of the sources and drains of the first, second and third MOS transistors except for the drain of the first MOS transistor.

REMARKS

Claims 1-13 are pending. The specification and claims 1 and 2 are amended.. A marked-up version showing the changes made by the present amendment is attached hereto as "**Version with markings to show changes made.**"

Claim 1 was rejected under 35 USC §102(e) as being anticipated by *Drowley et al.* Favorable reconsideration of this rejection is requested in view of the amendments made herein.